## General Description

This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for electronic ballast and switching mode power supplies.

## FEATURES

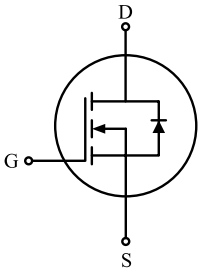
- $V_{DSS(Min.)}$= 500V, $I_D$= 9A
- Drain-Source ON Resistance : $R_{DS(ON)}$=0.8 Ω @$V_{GS}$ =10V
- Qg(typ.) =34.6nC

## MAXIMUM RATING (Tc=25℃)

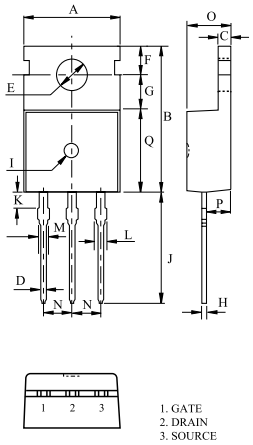
| CHARACTERISTIC | | SYMBOL | RATING | | UNIT |
|---|---|---|---|---|---|
| | | | KHB9D0N50P1 | KHB9D0N50F1 KHB9D0N50F2 | |
| Drain-Source Voltage | | $V_{DSS}$ | 500 | | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±30 | | V |
| Drain Current | @$T_C$=25℃ | $I_D$ | 9 | 9* | A |
| | @$T_C$=100℃ | | 5.4 | 5.4* | |
| | Pulsed (Note1) | $I_{DP}$ | 36 | 36* | |
| Single Pulsed Avalanche Energy (Note 2) | | $E_{AS}$ | 360 | | mJ |
| Repetitive Avalanche Energy (Note 1) | | $E_{AR}$ | 13.5 | | mJ |
| Peak Diode Recovery dv/dt (Note 3) | | dv/dt | 4.5 | | V/ns |
| Drain Power Dissipation | Tc=25℃ | $P_D$ | 135 | 44 | W |
| | Derate above25℃ | | 1.07 | 0.35 | W/℃ |
| Maximum Junction Temperature | | $T_j$ | 150 | | ℃ |
| Storage Temperature Range | | $T_{stg}$ | -55 150 | | ℃ |
| Thermal Characteristics | | | | | |
| Thermal Resistance, Junction-to-Case | | $R_{thJC}$ | 0.93 | 2.86 | ℃/W |
| Thermal Resistance, Case-to-Sink | | $R_{thCS}$ | 0.5 | - | ℃/W |
| Thermal Resistance, Junction-to-Ambient | | $R_{thJA}$ | 62.5 | 62.5 | ℃/W |

* : Drain current limited by maximum junction temperature.

## PIN CONNECTION



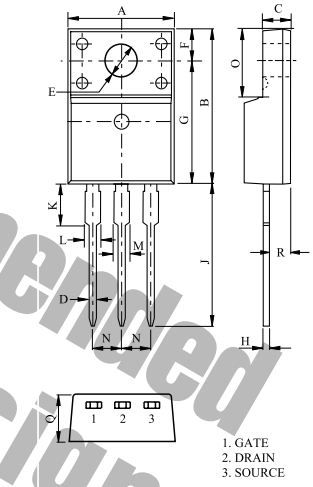

KHB9D0N50P1




| DIM | MILLIMETERS |
|---|---|
| A | 9.9 ± 0.2 |
| B | 15.95 MAX |
| C | 1.3+0.1/-0.05 |
| D | 0.8 ± 0.1 |
| E | ø3.6 ± 0.2 |
| F | 2.8 ± 0.1 |
| G | 3.7 |
| H | 0.5+0.1/-0.05 |
| I | ø1.5 |
| J | 13.08 ± 0.3 |
| K | 1.46 |
| L | 1.4 ± 0.1 |
| M | 1.27 ± 0.1 |
| N | 2.54 ± 0.2 |
| O | 4.5 ± 0.2 |
| P | 2.4 ± 0.2 |
| Q | 9.2 ± 0.2 |

TO-220AB

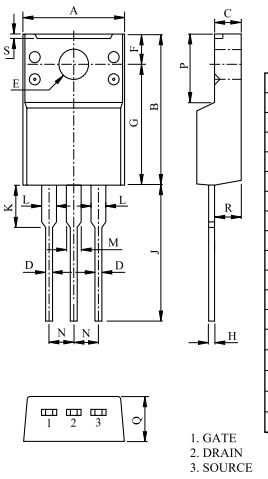
KHB9D0N50F1




| DIM | MILLIMETERS |
|---|---|
| A | 10.16 ± 0.2 |
| B | 15.87 ± 0.2 |
| C | 2.54 ± 0.2 |
| D | 0.8 ± 0.1 |
| E | ø3.18 ± 0.1 |
| F | 3.3 ± 0.1 |
| G | 12.57 ± 0.2 |
| H | 0.5 ± 0.1 |
| J | 13.0 MAX |
| K | 3.23 ± 0.1 |
| L | 1.47 MAX |
| M | 1.47 MAX |
| N | 2.54 ± 0.2 |
| O | 6.68 ± 0.2 |
| Q | 4.7 ± 0.2 |
| R | 2.76 ± 0.2 |

TO-220IS (1)

KHB9D0N50F2




| DIM | MILLIMETERS |
|---|---|
| A | 10.0±0.3 |
| B | 15.0±0.3 |
| C | 2.70±0.3 |
| D | 0.76+0.09/-0.05 |
| E | Φ3.2±0.2 |
| F | 3.0±0.3 |
| G | 12.0±0.3 |
| H | 0.5+0.1/-0.05 |
| J | 13.6±0.5 |
| K | 3.7±0.2 |
| L | 1.2+0.25/-0.1 |
| M | 1.5+0.25/-0.1 |
| N | 2.54±0.1 |
| P | 6.8±0.1 |
| Q | 4.5±0.2 |
| R | 2.6±0.2 |
| S | 0.5 Typ |

TO-220IS

ELECTRICAL CHARACTERISTICS (Tc=25℃)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $I_D$=250 μA, $V_{GS}$=0V | 500 | - | - | V |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_j$ | $I_D$=250 μA, Referenced to 25℃ | - | 0.57 | - | V/℃ |
| Drain Cut-off Current | $I_{DSS}$ | $V_{DS}$=500V, $V_{GS}$=0V, | - | - | 10 | μA |
| Gate Threshold Voltage | $V_{th}$ | $V_{DS}$=$V_{GS}$, $I_D$=250 μA | 2.0 | - | 4.0 | V |
| Gate Leakage Current | $I_{GSS}$ | $V_{GS}$=±30V, $V_{DS}$=0V | - | - | ±100 | nA |
| Drain-Source ON Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=4.5A | - | 0.65 | 0.8 | Ω |
| Dynamic | | | | | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$=400V, $I_D$=9A<br>$V_{GS}$=10V (Note4,5) | - | 34.6 | 40 | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 5.9 | - | |
| Gate-Drain Charge | $Q_{gd}$ | | - | 15.5 | - | |
| Turn-on Delay time | $t_{d(on)}$ | $V_{DD}$=200V<br>$R_L$=22Ω<br>$R_G$=25Ω (Note4,5) | - | 23 | 45 | ns |
| Turn-on Rise time | $t_r$ | | - | 65 | 140 | |
| Turn-off Delay time | $t_{d(off)}$ | | - | 148 | 241 | |
| Turn-off Fall time | $t_f$ | | - | 81 | 140 | |
| Input Capacitance | $C_{iss}$ | $V_{DS}$=25V, $V_{GS}$=0V, f=1.0MHz | - | 1389 | 1805 | pF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 19.2 | 24.9 | |
| Output Capacitance | $C_{oss}$ | | - | 155.7 | 202 | |
| Source-Drain Diode Ratings | | | | | | |
| Continuous Source Current | $I_S$ | $V_{GS}$<$V_{th}$ | - | - | 9 | A |
| Pulsed Source Current | $I_{SP}$ | | - | - | 36 | |
| Diode Forward Voltage | $V_{SD}$ | $I_S$=9A, $V_{GS}$=0V | - | - | 1.5 | V |
| Reverse Recovery Time | $t_{rr}$ | $I_S$=9A, $V_{GS}$=0V,<br>dIs/dt=100A/μs | - | 357 | - | ns |
| Reverse Recovery Charge | $Q_{rr}$ | | - | 4.87 | - | μC |



Note 1) Repetivity rating : Pulse width limited by junction temperature.

Note 2) L = 8mH, $I_S$=9A, $V_{DD}$=50V, $R_G$ = 25Ω, Starting $T_j$ = 25℃.

Note 3) $I_S$ ≤9A, dI/dt≤200A/μs, $V_{DD}$≤$BV_{DSS}$, Starting $T_j$ = 25℃.

Note 4) Pulse Test : Pulse width ≤ 300μs, Duty Cycle ≤ 2%.

Note 5) Essentially independent of operating temperature.

Fig1. $I_D$ - $V_{DS}$

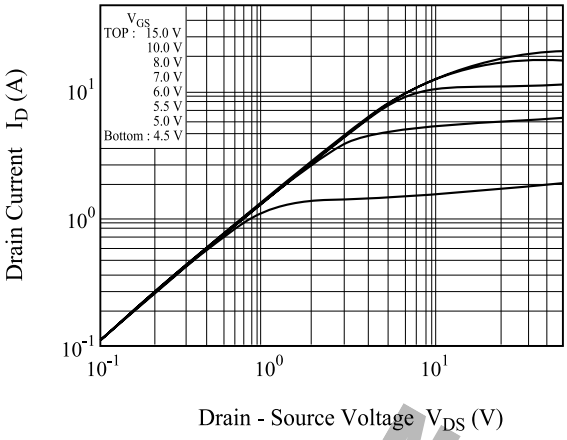



Fig2. $I_D$ - $V_{GS}$

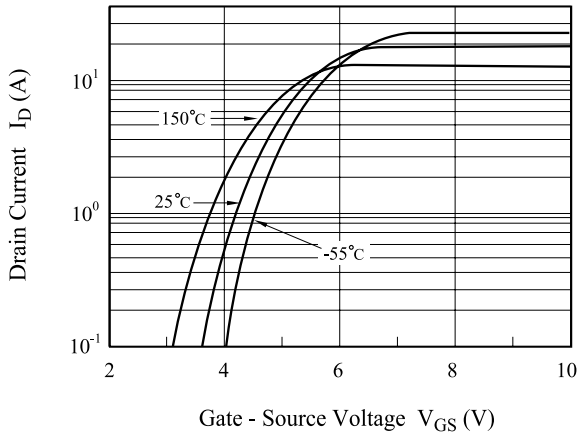





Fig3. $BV_{DSS}$ - $T_j$

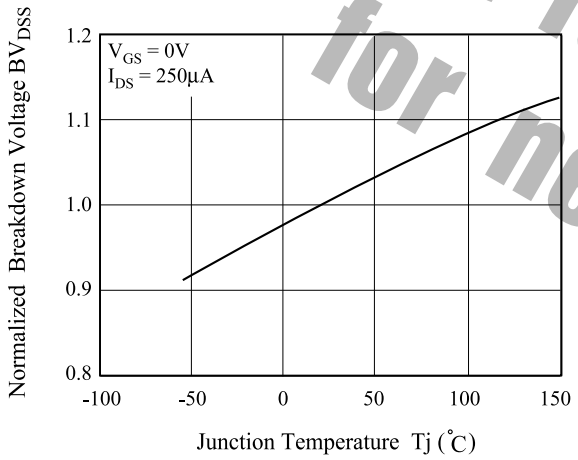



Fig4. $R_{DS(ON)}$ - $I_D$

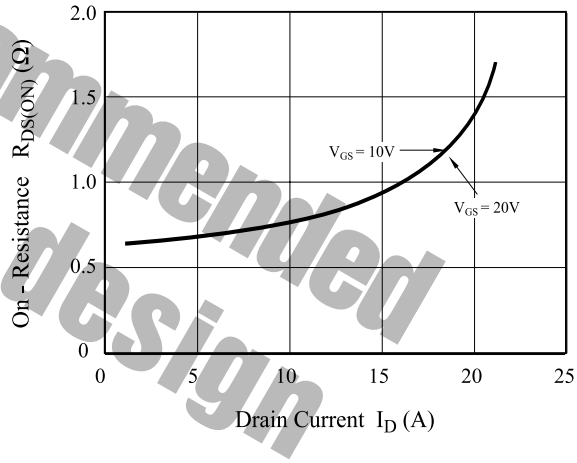



Fig5. $I_S$ - $V_{SD}$

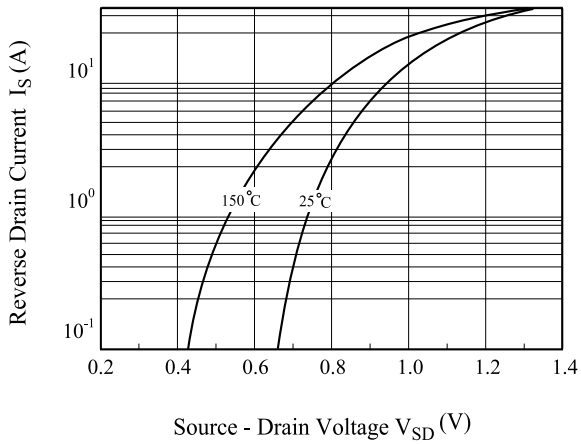



Fig6. $R_{DS(ON)}$ - $T_j$

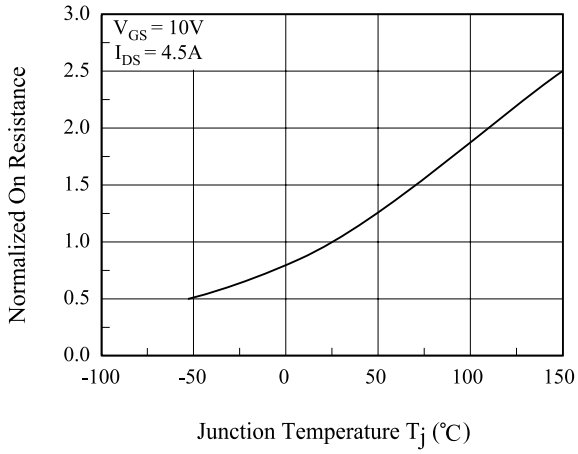


Fig7. C - $V_{DS}$

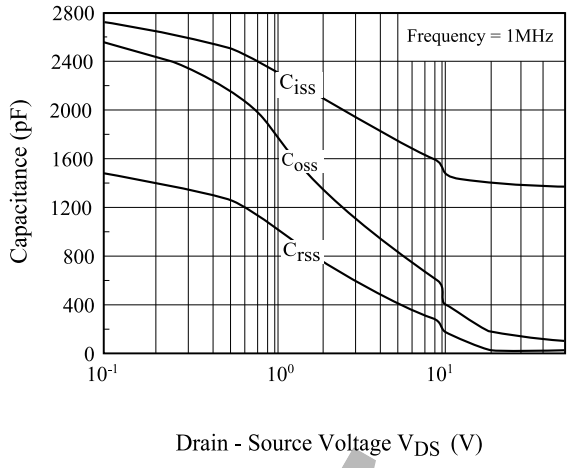



Fig8. $Q_g$- $V_{GS}$

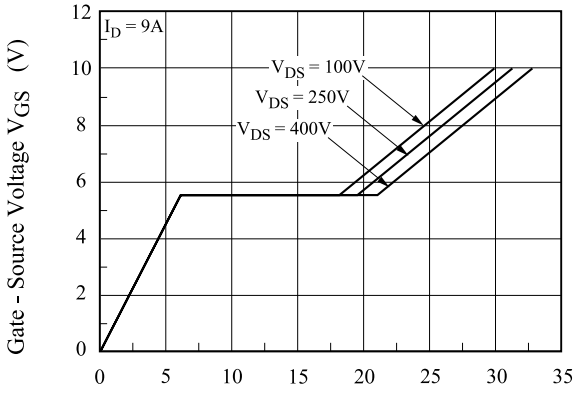



Fig9. Safe Operation Area

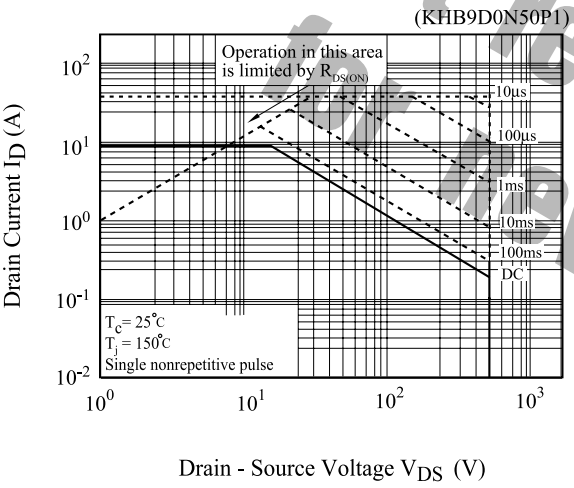



Fig10. Safe Operation Area

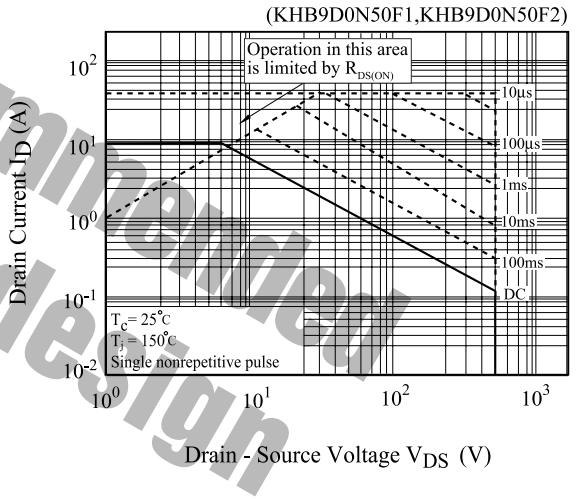





Fig11. $I_D$ - $T_j$

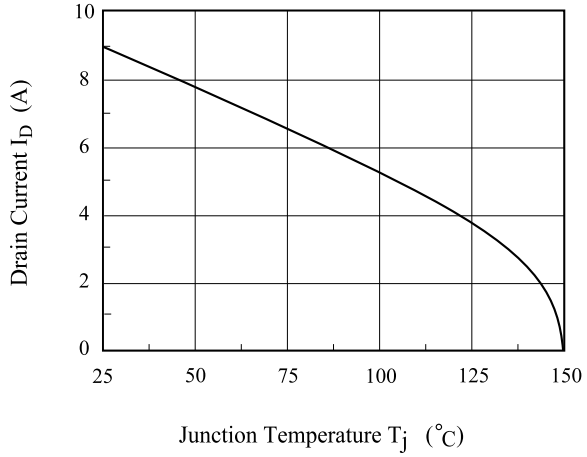


Fig12. Transient Thermal Response Curve

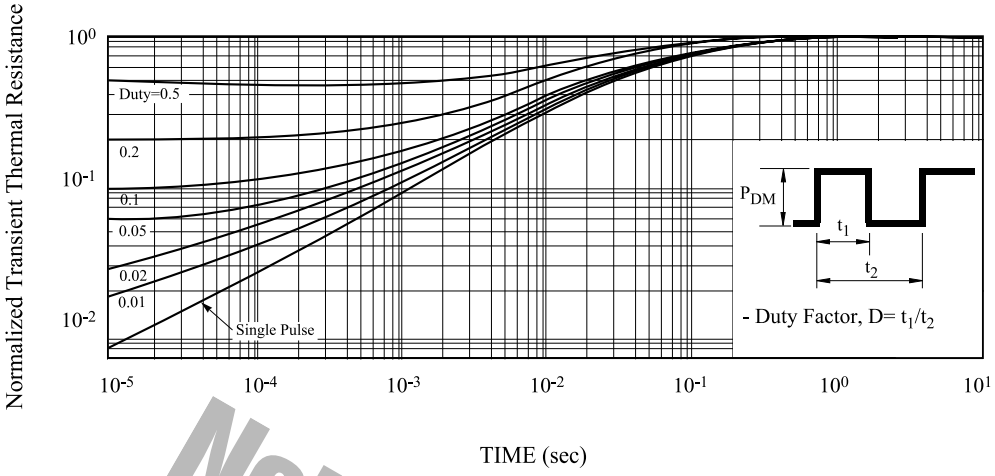





Fig13. Transient Thermal Response Curve

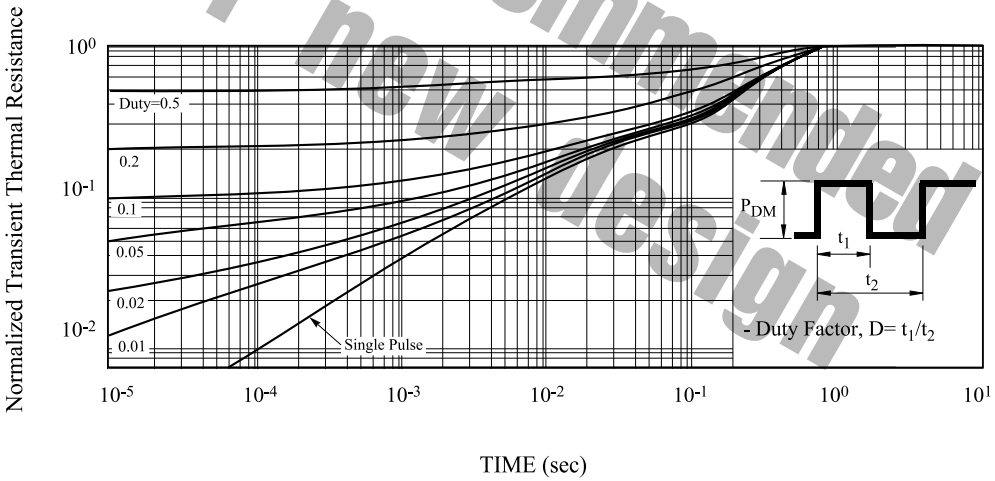
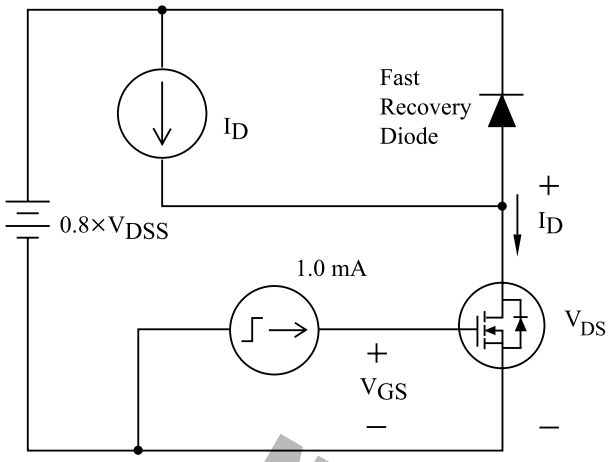


Fig14. Gate Charge



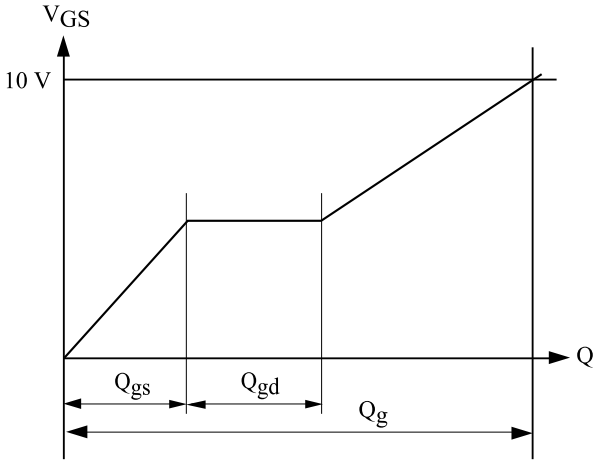
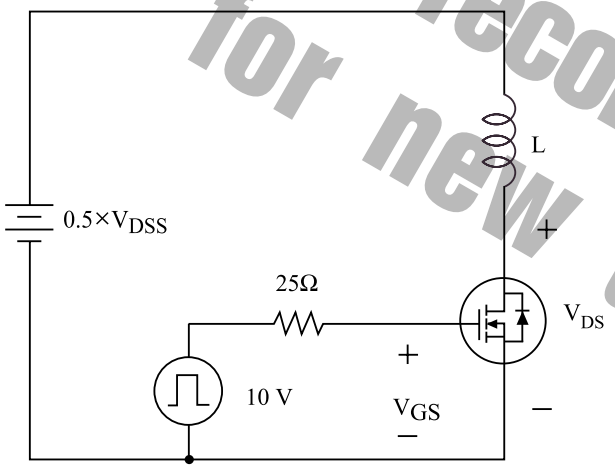






Fig15. Single Pulsed Avalanche Energy




$$E_{AS}=\frac{1}{2}\,LI_{AS}^2\,\frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

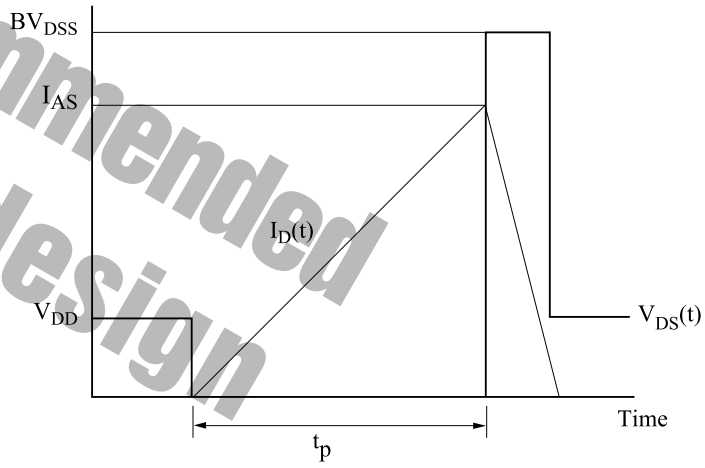
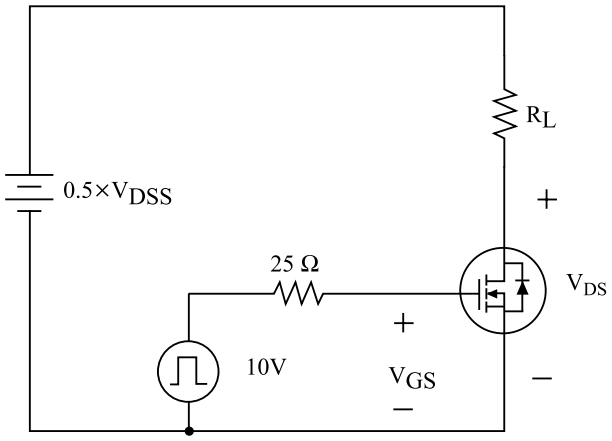



Fig16. Resistive Load Switching



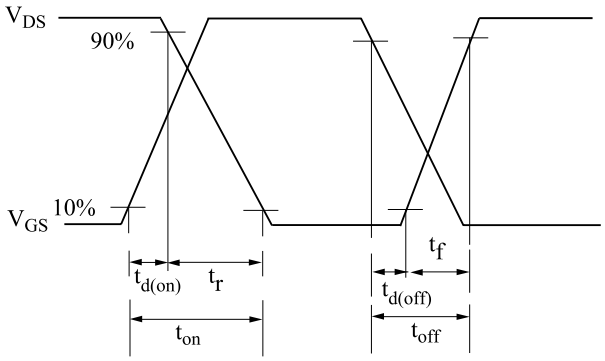



Fig17. Source - Drain Diode Reverse Recovery and dv /dt